



ALPHA & OMEGA
SEMICONDUCTOR



AO6605

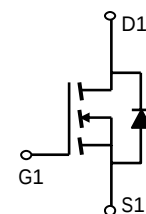
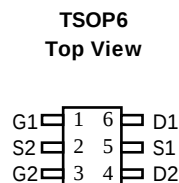
Complementary Enhancement Mode Field Effect Transistor

General Description

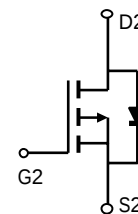
The AO6605 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. The complementary MOSFETs form a high-speed power inverter, suitable for a multitude of applications. Standard Product AO6605 is Pb-free (meets ROHS & Sony 259 specifications). AO6605L is a Green Product ordering option. AO6605 and AO6605L are electrically identical.

Features

n-channel	p-channel
V_{DS} (V) = 20V	-20V
I_D = 1.9A (V_{GS} = 4.5V)	-2.5A
$R_{DS(ON)}$	
< 200m Ω	< 97m Ω (V_{GS} = 4.5V)
< 270m Ω	< 130m Ω (V_{GS} = 2.5V)
< 400m Ω	< 190m Ω (V_{GS} = 1.8V)



n-channel



p-channel

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Max n-channel	Max p-channel	Units
Drain-Source Voltage	V_{DS}	20	-20	V
Gate-Source Voltage	V_{GS}	± 8	± 8	V
Continuous Drain Current ^A	$T_A=25^\circ\text{C}$	1.7	-2.5	A
	$T_A=70^\circ\text{C}$	1.4	-2.0	
Pulsed Drain Current ^B	I_{DM}	15	-15	
Power Dissipation	$T_A=25^\circ\text{C}$	1.15	1.15	W
	$T_A=70^\circ\text{C}$	0.73	0.73	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	-55 to 150	$^\circ\text{C}$

Thermal Characteristics: n-channel and p-channel

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	78	110	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A		106	150	$^\circ\text{C/W}$
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	64	80	$^\circ\text{C/W}$

N-channel MOSFET Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	20			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=16\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^{\circ}\text{C}$			1 5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 8\text{V}$			25	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	0.5	0.55	0.9	V
$I_{D(ON)}$	On state drain current	$V_{GS}=4.5\text{V}$, $V_{DS}=5\text{V}$	5			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=4.5\text{V}$, $I_D=1.9\text{A}$ $T_J=125^{\circ}\text{C}$		165 230	200 280	$\text{m}\Omega$
		$V_{GS}=2.5\text{V}$, $I_D=1.6\text{A}$		225	270	$\text{m}\Omega$
		$V_{GS}=1.8\text{V}$, $I_D=1.3\text{A}$		325	400	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=1.9\text{A}$		2.8		S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}$, $V_{GS}=0\text{V}$		0.88	1	V
I_S	Maximum Body-Diode Continuous Current				0.4	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=10\text{V}$, $f=1\text{MHz}$		101	125	pF
C_{oss}	Output Capacitance			17		pF
C_{rss}	Reverse Transfer Capacitance			14		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		3	4	Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	$V_{GS}=4.5\text{V}$, $V_{DS}=10\text{V}$, $I_D=1.9\text{A}$		1.6	2	nC
Q_{gs}	Gate Source Charge			0.2		nC
Q_{gd}	Gate Drain Charge			0.4		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=5\text{V}$, $V_{DS}=10\text{V}$, $R_L=5.3\Omega$, $R_{GEN}=3\Omega$		3.2		ns
t_r	Turn-On Rise Time			4		ns
$t_{D(off)}$	Turn-Off DelayTime			15.5		ns
t_f	Turn-Off Fall Time			2.4		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=1.9\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		6.7	16	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=1.9\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		1.6		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The value in any given application depends on the user's specific board design. The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The SOA curve provides a single pulse rating.

Rev2: August 2005

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N-CHANNEL TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

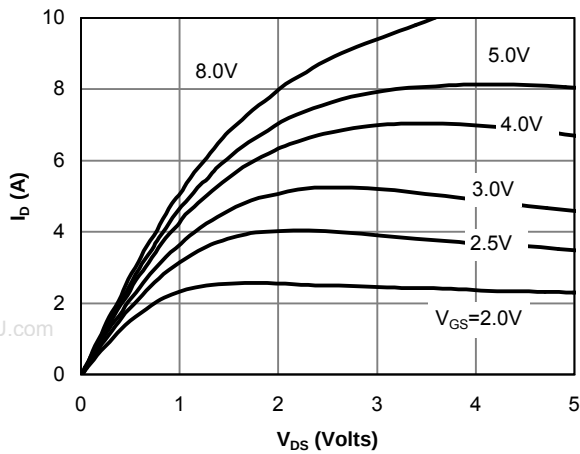


Fig 1: On-Region Characteristics

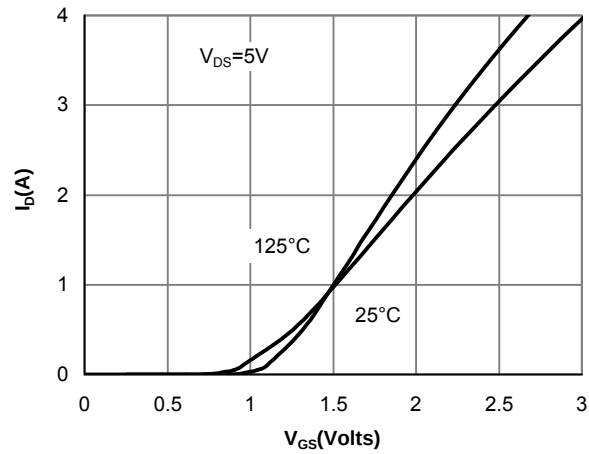


Figure 2: Transfer Characteristics

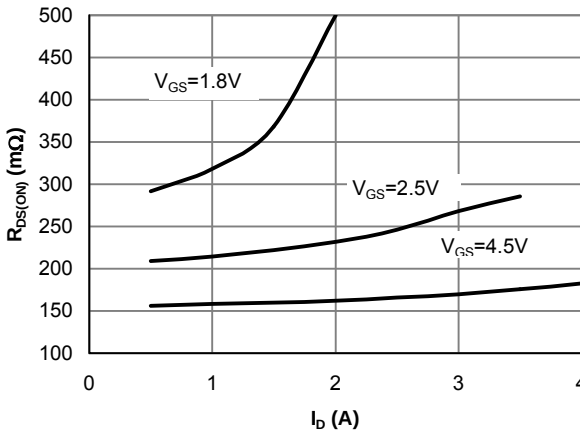


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

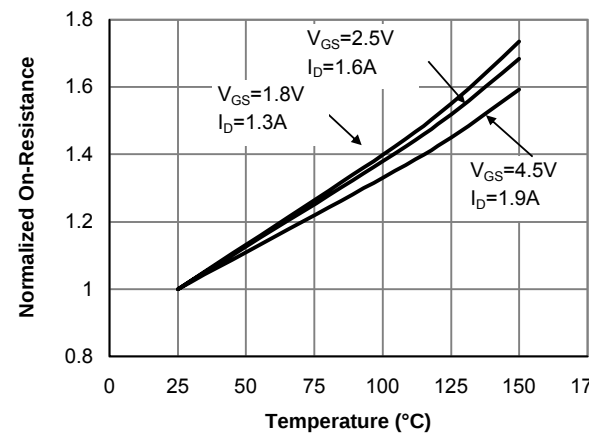


Figure 4: On-Resistance vs. Junction Temperature

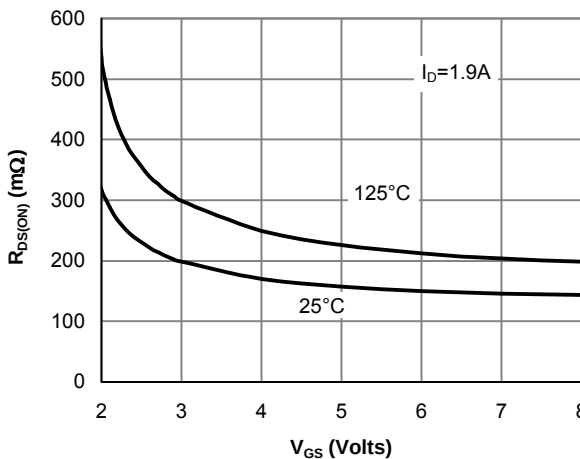


Figure 5: On-Resistance vs. Gate-Source Voltage

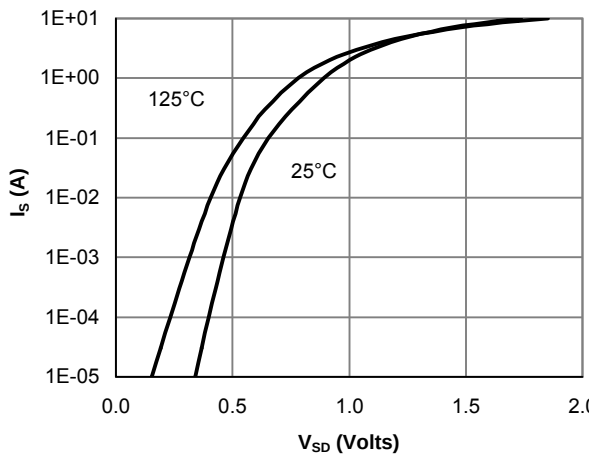


Figure 6: Body-Diode Characteristics

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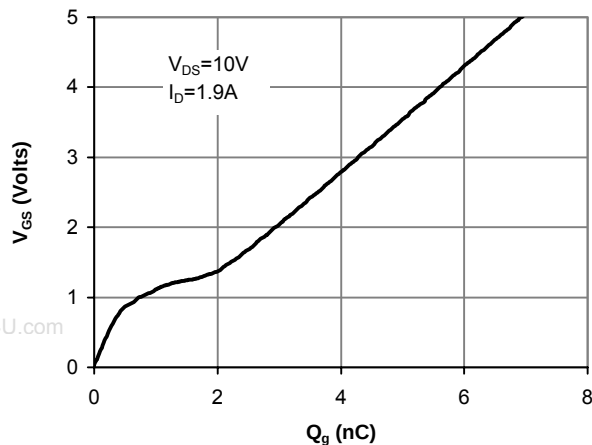


Figure 7: Gate-Charge Characteristics

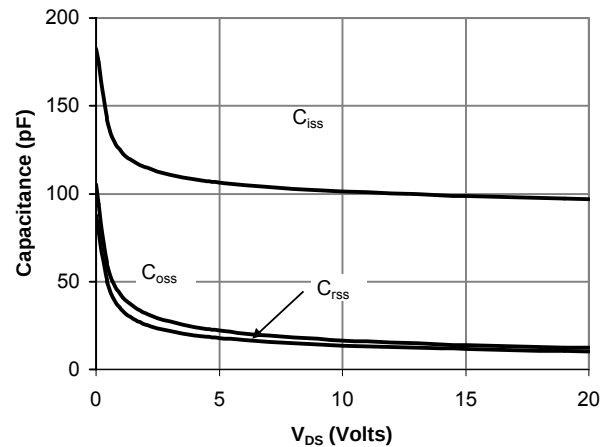


Figure 8: Capacitance Characteristics

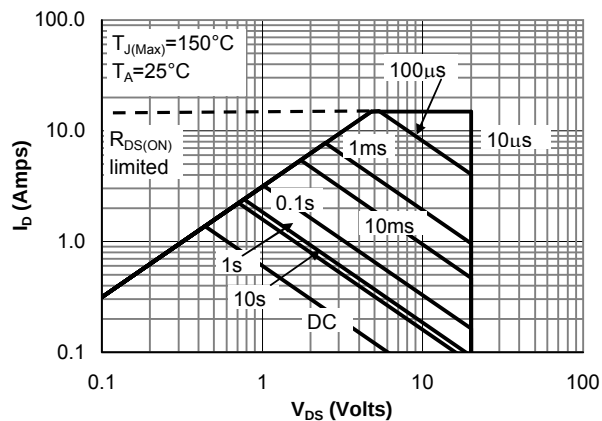


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

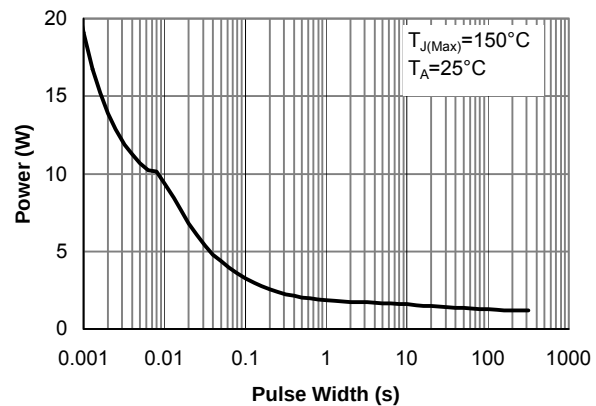


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

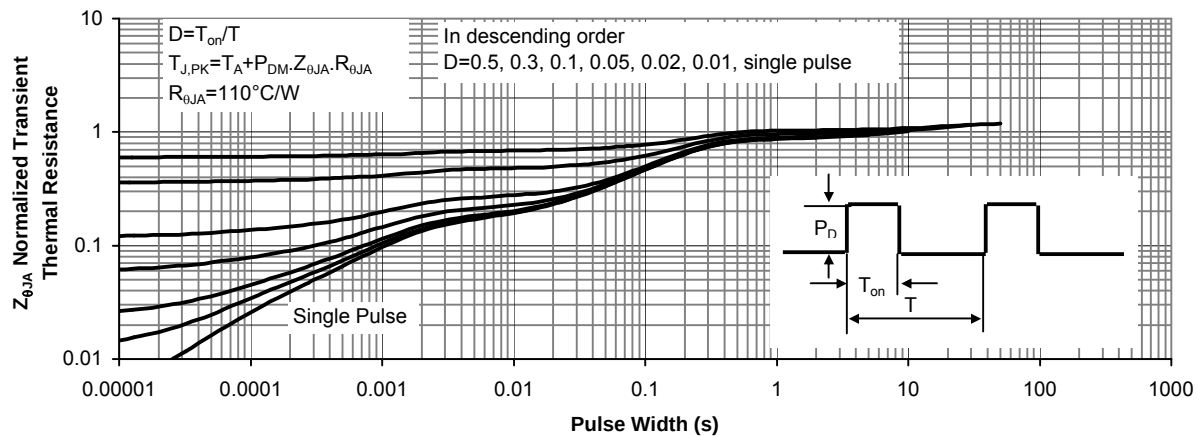


Figure 11: Normalized Maximum Transient Thermal Impedance

P-channel MOSFET Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}$, $V_{GS}=0\text{V}$	-20			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-16\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			-1 -5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 8\text{V}$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=-250\mu\text{A}$	-0.3	-0.55	-1	V
$I_{D(ON)}$	On state drain current	$V_{GS}=-4.5\text{V}$, $V_{DS}=-5\text{V}$	-15			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-4.5\text{V}$, $I_D=-2.5\text{A}$ $T_J=125^\circ\text{C}$		81 111	97 135	$\text{m}\Omega$
		$V_{GS}=-2.5\text{V}$, $I_D=-2\text{A}$		108	130	$\text{m}\Omega$
		$V_{GS}=-1.8\text{V}$, $I_D=-1\text{A}$		146	190	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=-5\text{V}$, $I_D=-3\text{A}$	4	6		S
V_{SD}	Diode Forward Voltage	$I_S=-1\text{A}$, $V_{GS}=0\text{V}$		-0.78	-1	V
I_S	Maximum Body-Diode Continuous Current				-2	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=-10\text{V}$, $f=1\text{MHz}$		540	700	pF
C_{oss}	Output Capacitance			72		pF
C_{rss}	Reverse Transfer Capacitance			49		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		15	19.5	Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	$V_{GS}=-4.5\text{V}$, $V_{DS}=-10\text{V}$, $I_D=-2.5\text{A}$		6.1	7.5	nC
Q_{gs}	Gate Source Charge			0.6		nC
Q_{gd}	Gate Drain Charge			1.6		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=-4.5\text{V}$, $V_{DS}=-10\text{V}$, $R_L=3.9\Omega$, $R_{GEN}=3\Omega$		12		ns
t_r	Turn-On Rise Time			15		ns
$t_{D(off)}$	Turn-Off DelayTime			49		ns
t_f	Turn-Off Fall Time			27		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=-2.5\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		22	26	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=-2.5\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		16		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any a given application depends on the user's specific board design. The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D: The static characteristics in Figures 1 to 6,12,14 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

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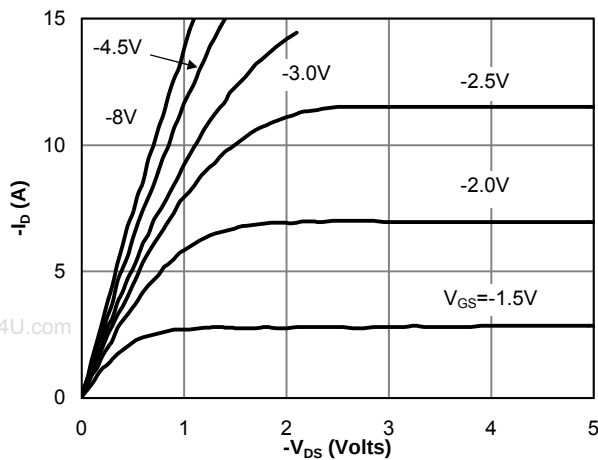


Fig 1: On-Region Characteristics

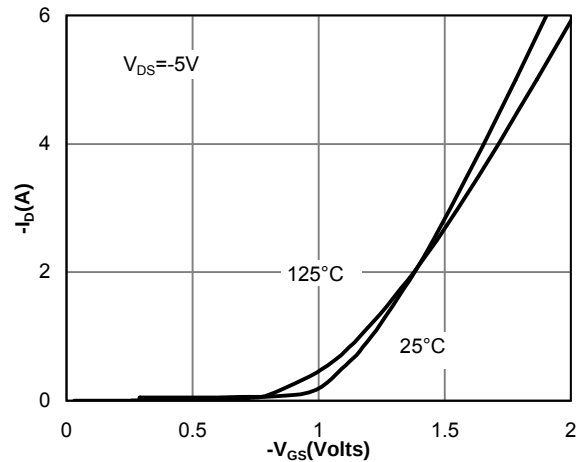


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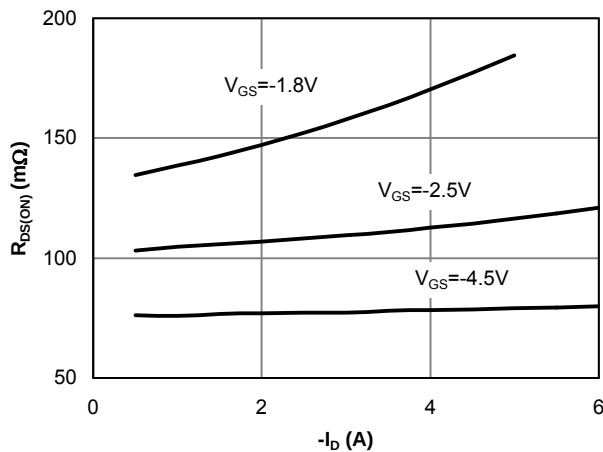


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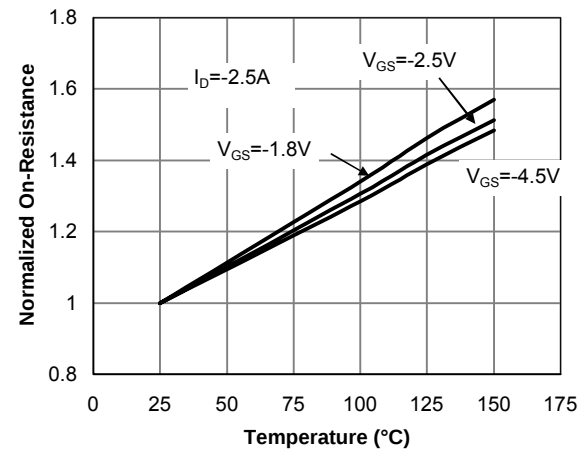


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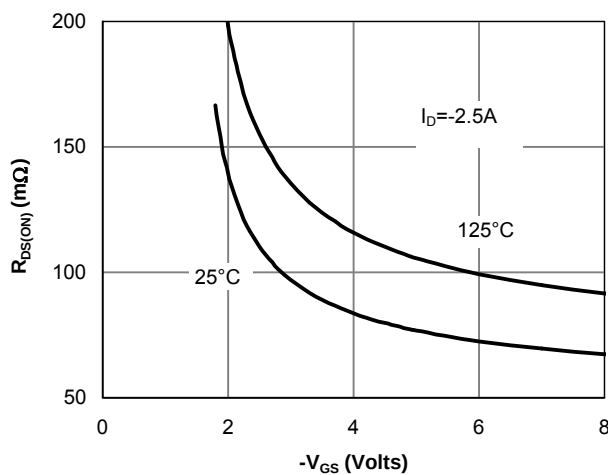


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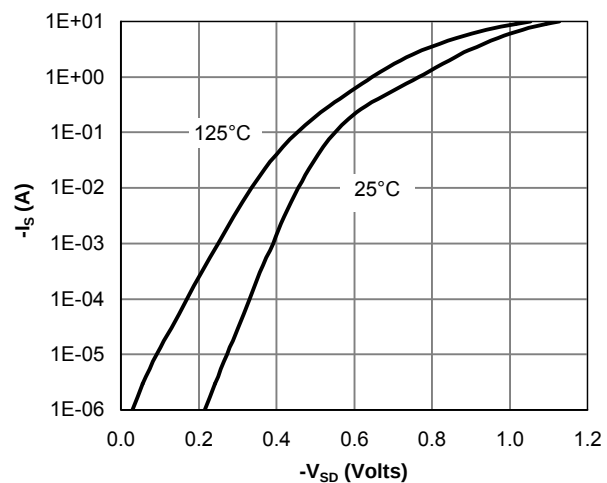


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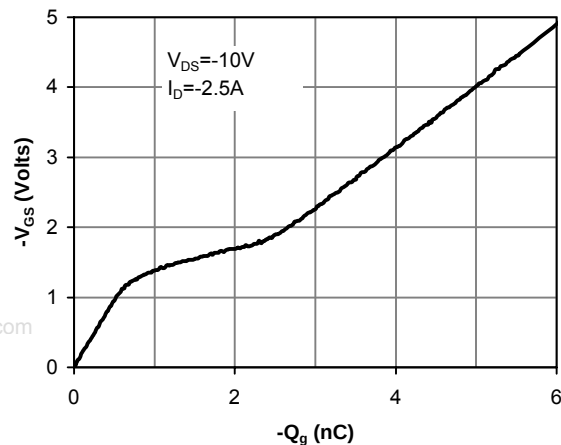


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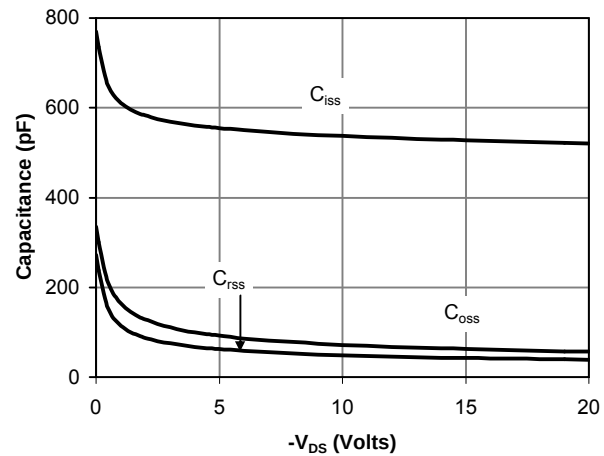


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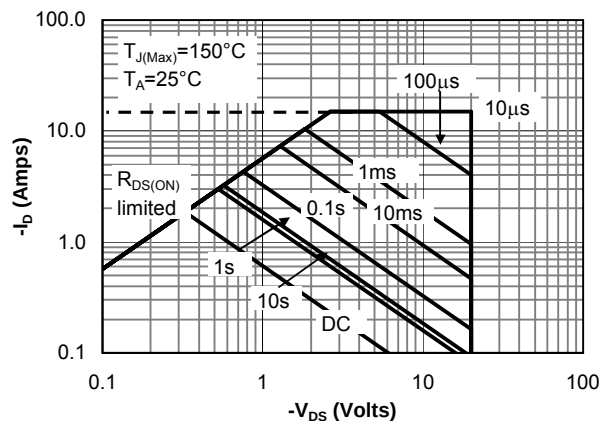


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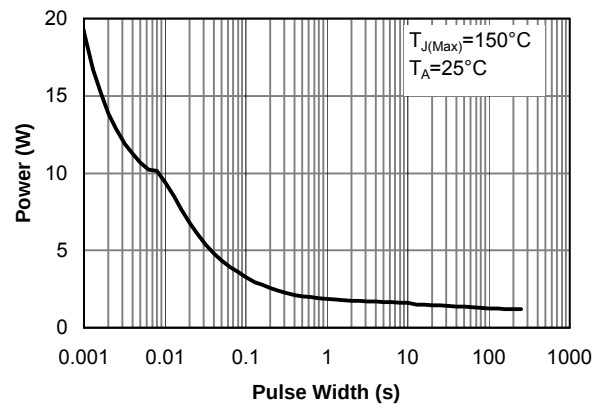


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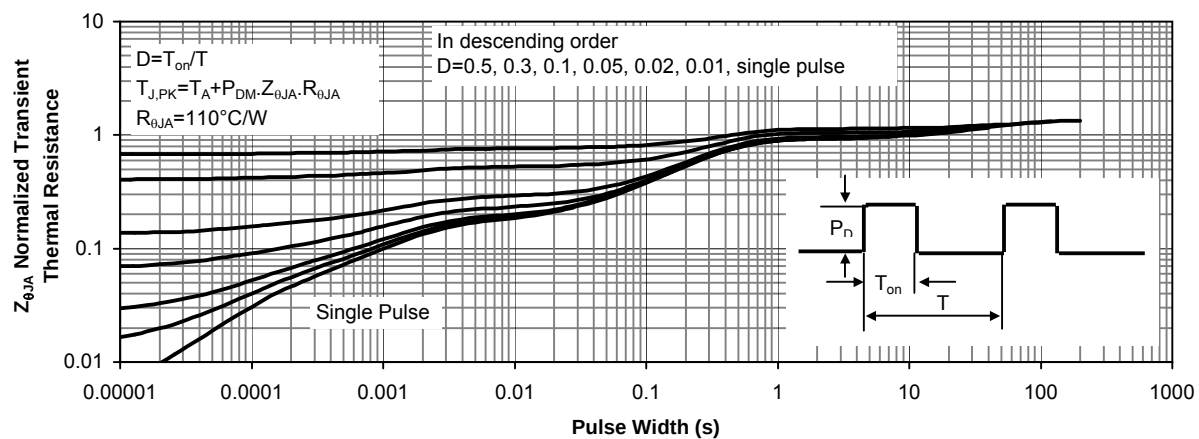


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